



# Memory Interface Electrical Validation LPDDR4

3/14/2016

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<http://www.mavin.com.tw>

免責聲明

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# Agenda

- DRAM Standard Basic – LPDDR4
- Signal Acquisition and Analysis – LPDDRx
- Questions



# DRAM Standard Basic – LPDDR4

3/14/2016

# Section Agenda

- DRAM Standard Basic – LPDDR4
  - Motivation
  - Overview (LPDDR3 – LPDDR4 Comparison)
  - Architecture
  - Pin Comparison
  - Training/Calibration
  - Parameter Definition
    - Vcent
    - Mask Parameters
    - tDIPW, VIH<sub>L</sub>\_AC
  - Read Write Timing
  - VSSQ Referenced Signaling
  - Beyond LPDDR4

# Key Factors Driving Mobile Eco-System

**Performance**

**Requiring over  
20GB/s BW**

*3 key factors are driving  
next mobile solutions*

**Power budget is  
critically necessary**

**Power Efficiency**

**Cost Budget**

**JEDEC**

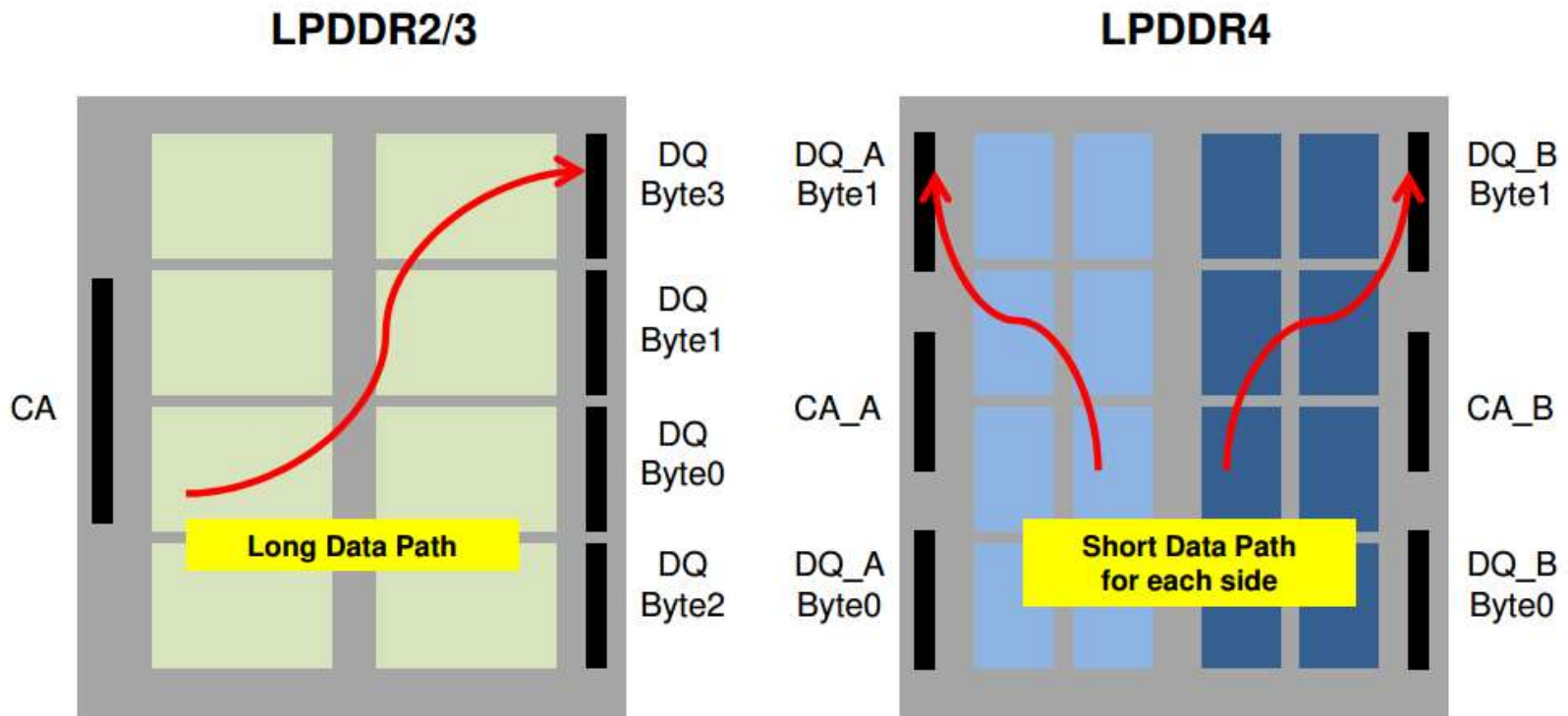
*Global Standards for the Microelectronics Industry*

# LPDDR4 Overview

	LPDDR3	LPDDR4	Notes
Channels	1 or 2	2	2 channels per die; LP4 channel = x16 Each LP4 channel has its own CA and Clock CA/Clock/DQ co-located on die
Clock Speed	400MHz to 1066MHz	800MHz to 2133MHz	Doubling the clock rate in LP4
Data Rate	800MT/s to 2133MT/s	1600MT/s to 4267MT/s	Doubling the data rate in LP4
Burst Length	8	16/32	Doubling Pre-fetch, core frequency is same
DQ ODT	No Termination, or 240/120 to VDDQ	VSSQ Termination	VSSQ = Ground
CA ODT	No Termination	VSSQ Termination	VSSQ = Ground
Vref	External	Internal	Vcent replaces Vref as reference for external measurements
Package	PoP/Discrete	PoP/Discrete	No change
I/O Voltage	1.2	1.1	Reduced Voltage
Preamble Postamble	Fixed	User selectable through MR	Makes it complicated to differentiate Read from Write
Voltage Swing	Close to rail/80%	~ 0.4 V	Reduced Swing
Read/Write Timing	Edge / Center Aligned	Edge/not Aligned	Writes need training for DQS to DQ relationship

# New Two Channel Dual Edge Pad Architecture

Reduced routing distance allows lower core power and high speed operation



# New Command Definition for Lower Pin Count

- CA pins (per channel) reduced from 10 to 6
- LPDDR4 CA bus runs SDR
- Two and four-cycle command encoding

SDRAM Command	SDR Command Pins		DDR CA pins (10)										CK_1 EDGE		
	CKE		CS_N	CA0	CA1	CA2	CA3	CA4	CA5	CA6	CA7	CA8		CA9	
	CK_t(n-1)	CK_t(n)		MA0	MA1	MA2	MA3	MA4	MA5	OP0	OP1	OP2		OP3	OP4
MRR	H	H	L	L	L	L	L	MA0	MA1	MA2	MA3	MA4	MA5		
MRR	H	H	L	L	L	L	H	MA0	MA1	MA2	MA3	MA4	MA5		
Refresh (per bank)	H	H	L	L	L	H	L	X	X	X	X	X	X		
Refresh (all bank)	H	H	L	L	L	H	H	X	X	X	X	X	X		
Enter Self Refresh	H	L	L	L	L	H	X	X	X	X	X	X	X		

LPDDR2/3

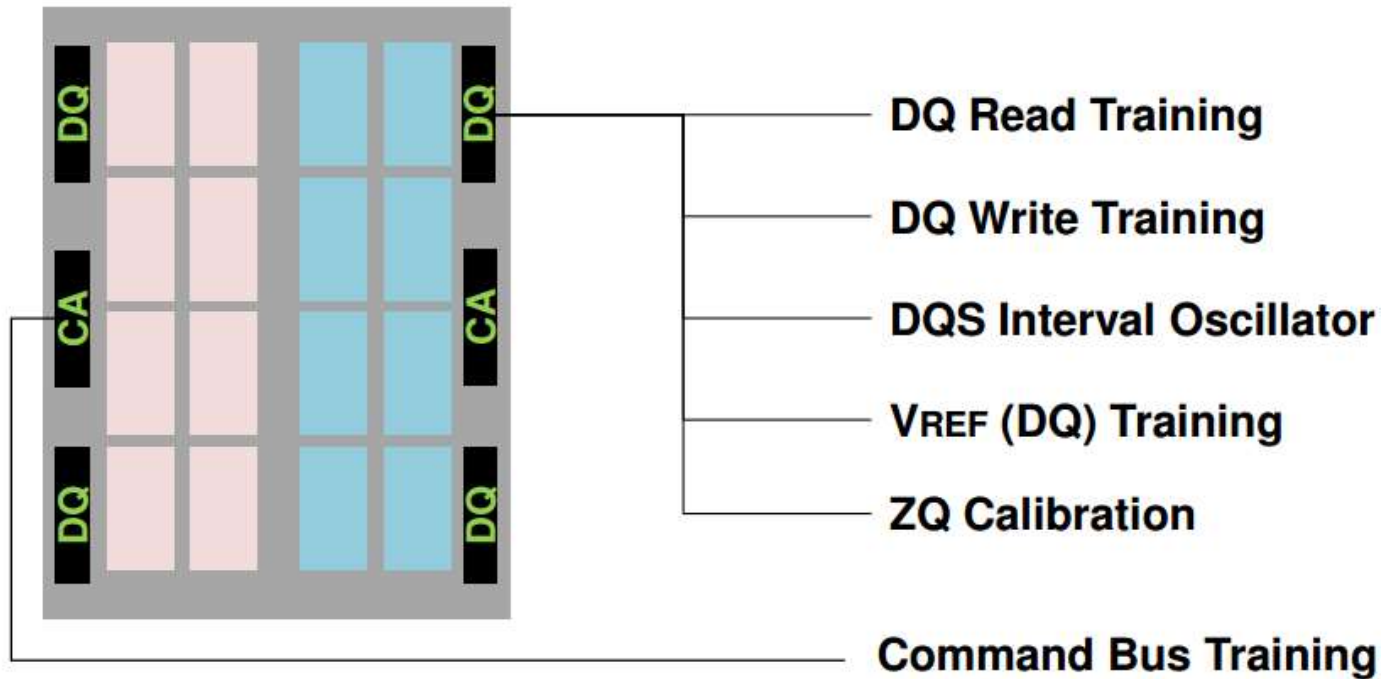
SDRAM Command	SDR Command Pins	SDR CA Pins (6)						CK_t edge	Notes
	CS	CA0	CA1	CA2	CA3	CA4	CA5		
RFU	H	L	H	H	H	H	V	R1	1,2
	L	V						R2	
Activate -1 (ACT-1)	H	H	L	R12	R13	R14	R15	R1	1,2,3,10
	L	BA0	BA1	BA2	V	R10	R11	R2	
Activate -2 (ACT-2)	H	H	H	R6	R7	R8	R9	R1	1,10
	L	R0	R1	R2	R3	R4	R5	R2	
Read -1 (RD-1)	H	L	H	L	L	L	BL	R1	1,2,3,6,7,9
	L	BA0	BA1	BA2	V	C9	AP	R2	
CAS-2 (Write-2, Mask Write-2, Read-2, MRR-2, MPC)	H	L	H	L	L	H	C8	R1	1,8,9
	L	C2	C3	C4	C5	C6	C7	R2	
RFU	H	L	H	L	H	L	V	R1	1,2
	L	V						R2	
	L	V						R1	

LPDDR4



# I/O Training / Calibration

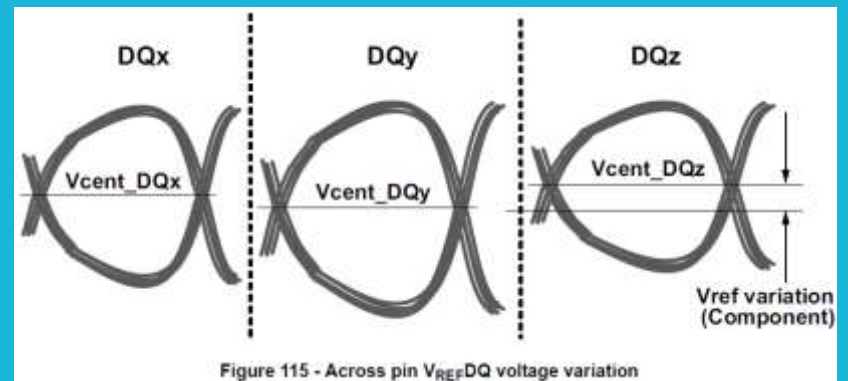
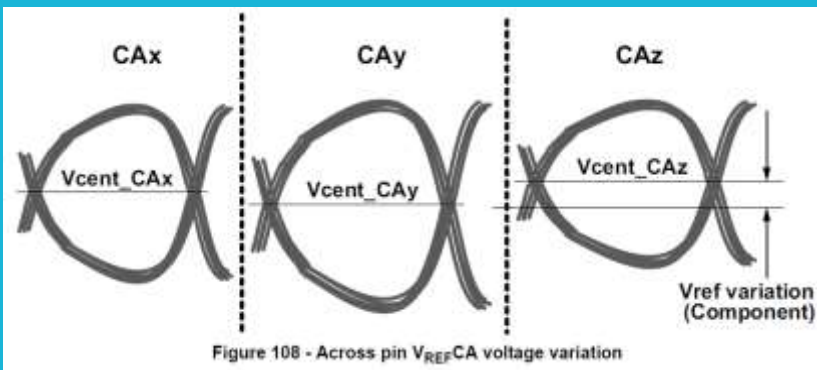
To enable high speed operation, various training are needed.



- Two Frequency Set Points enable Rapid Frequency Switching
  - Stores calibration/training values at different frequencies
  - FSP settings can be saved and loaded via MR

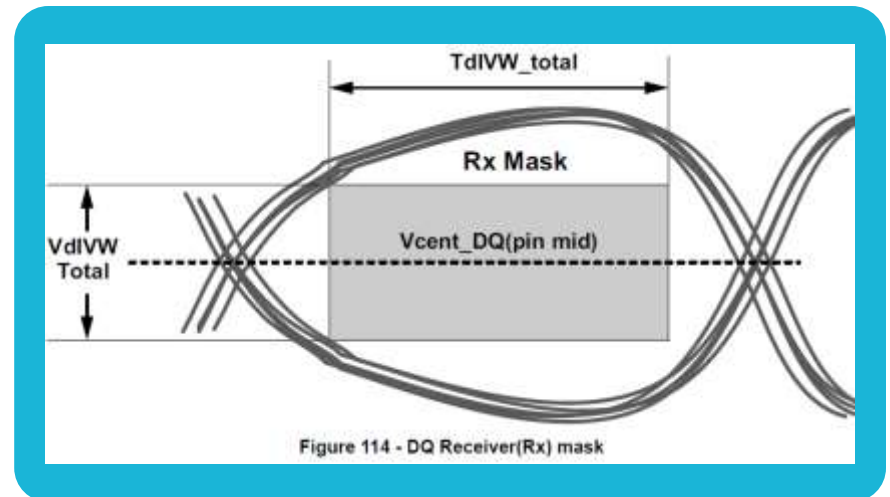
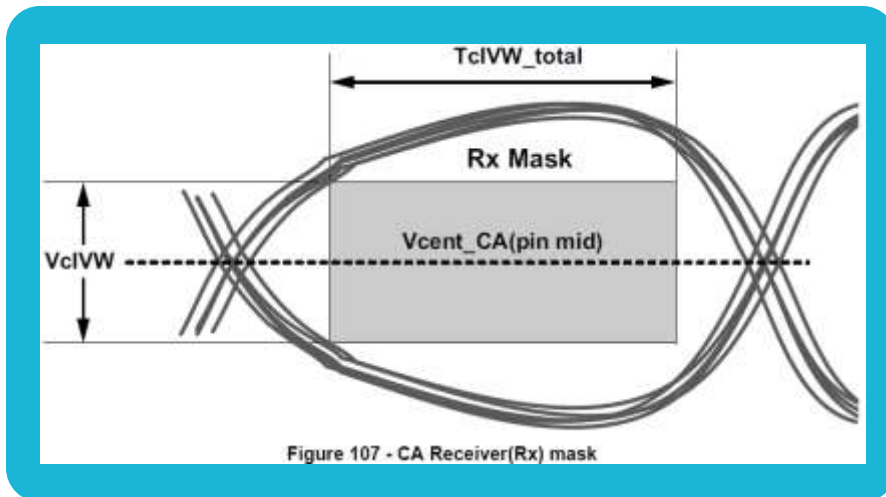
# CA Bus / DQ Bus Vcent

- LPDDR4 bus does not include (externally accessible) VREF.
- $V_{cent\_CAx} / V_{cent\_DQx}$  is the Voltage at which the cumulative eye of the pin  $CAx / DQx$  is widest
- $V_{cent\_CA(pin\_mid)} / V_{cent\_DQ(pin\_mid)}$  is defined as the middle between the largest and smallest  $V_{cent\_CA} / V_{cent\_DQ}$  within the group.
- $V_{cent\_CA(pin\_mid)} / V_{cent\_DQ(pin\_mid)}$  is the best available estimate for the internal VREF (after training), that is accessible at the pins.



# CA Bus / DQ Bus Mask-Based Timing and Voltage Definition

- All voltages are referenced to  $V_{cent}$
- All timing referenced to **rising clock edge** / **strobe edges**
- Mask is centered around  $V_{cent}$  and **rising clock edge** / **strobe edges**

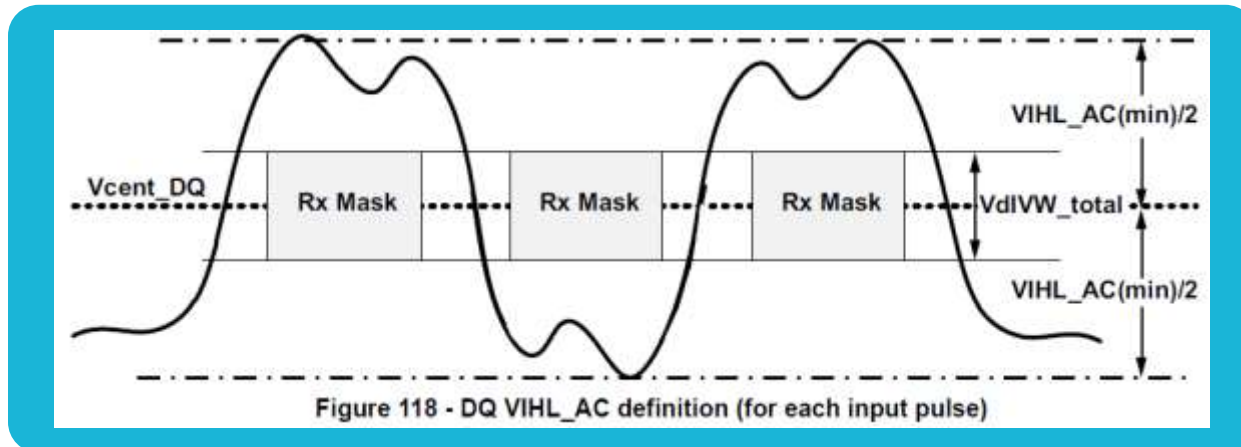
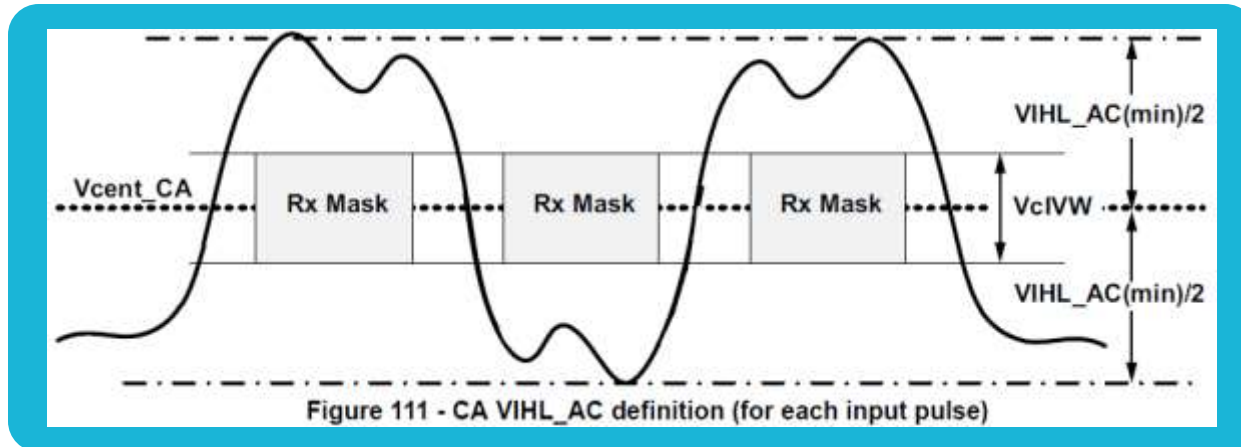


Conditions must be met cumulatively per group over time

# CA Bus / DQ Bus

## Minimum Voltage Level and Input Valid Window

- All voltages are referenced to  $V_{cent}$

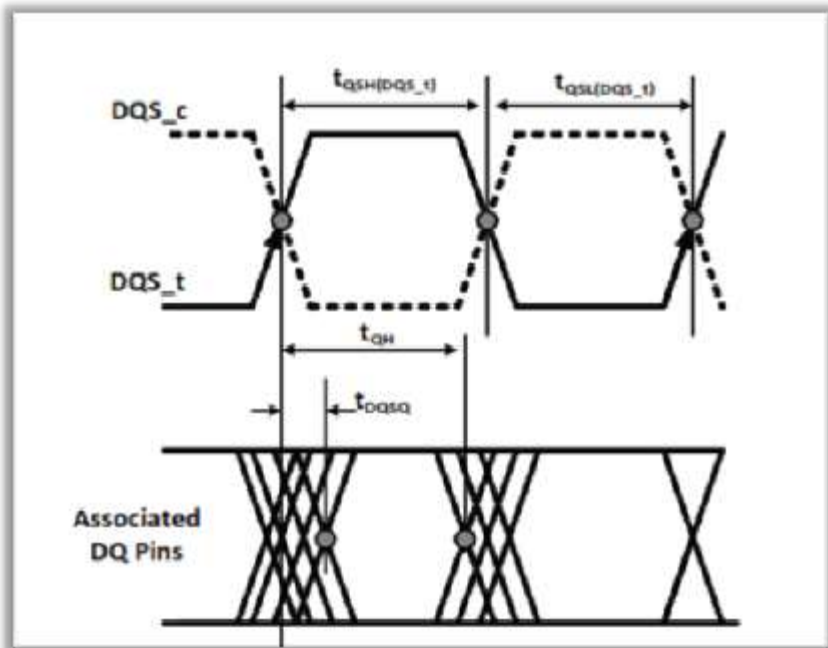


Conditions must be met for each individual UI

# Read / Write Timing

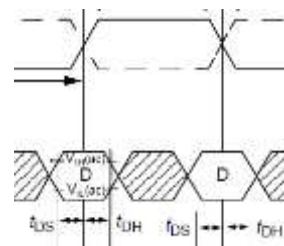
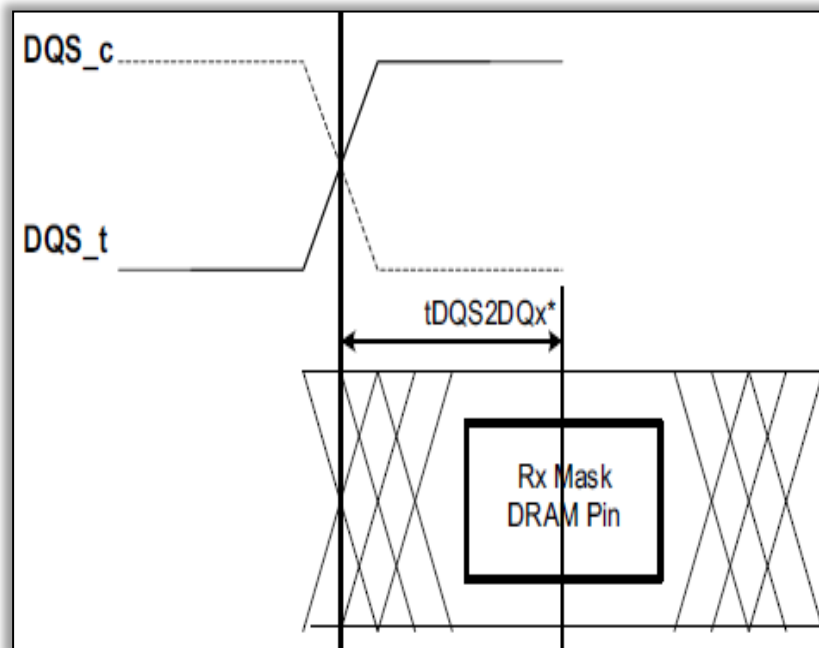
Read

Data nominally EDGE aligned to strobe; similar to LPDDR2/3



Write

Data offset to strobe by  $t_{DQS2DQ}$ ; different from LPDDR2/3



For reference:  
LPDDR2/3: center aligned

# Voltage and Timing Numbers

## Data: DDR

\* UI=tCK(avg)min/2

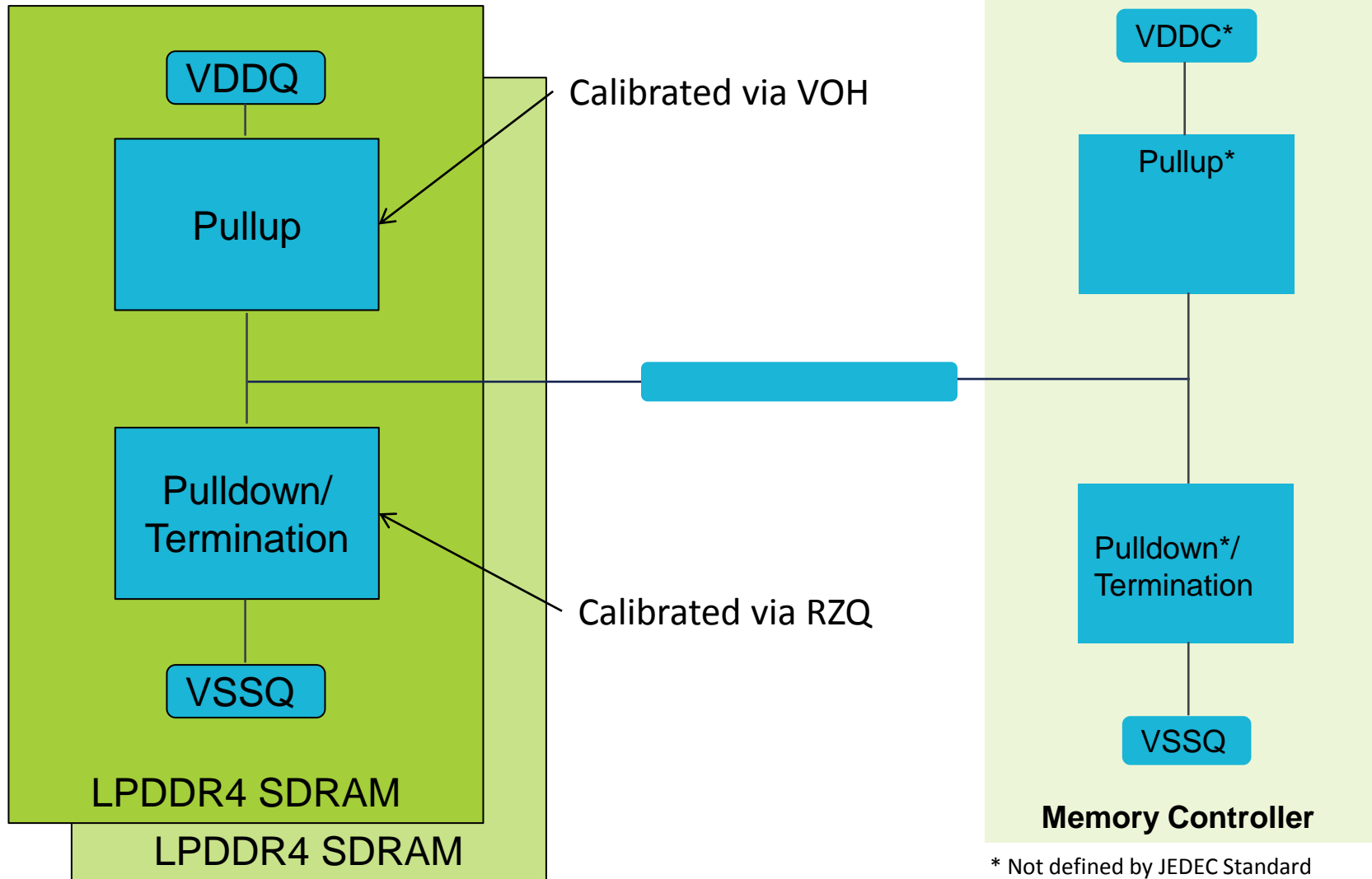
Symbol	Parameter	1600/1867 <sup>A</sup>		2133/2400		3200		4266		Unit	NOTE
		min	max	min	max	min	max	min	max		
VdIVW_total	Rx Mask voltage - p-p total	-	140	-	140	-	140	-	120	mV	1,2,3,5
TdIVW_total	Rx timing window total (At VdIVW voltage levels)	-	0.22	-	0.22	-	0.25	-	0.25	UI*	1,2,4,5
TdIVW_1bit	Rx timing window 1 bit toggle (At VdIVW voltage levels)	-	TBD	-	TBD	-	TBD	-	TBD	UI*	1,2,4,5,14
VIHL_AC	DQ AC input pulse amplitude pk-pk	180	-	180	-	180	-	170	-	mV	7,15
TdIPW_DQ	Input pulse width (At Vcent_DQ)	0.45		0.45		0.45		0.45		UI*	8
tDQS2DQ	DQ to DQS offset	200	800	200	800	200	800	200	800	ps	9

## CA: SDR

\* UI=tck(avg)min

Symbol	Parameter	DQ-1333 <sup>A</sup>		DQ-1600/1867		DQ-3200		DQ-4266		Unit	NOTE
		min	max	min	max	min	max	min	max		
VcIVW	Rx Mask voltage - p-p	-	175	-	175	-	155	-	145	mV	1,2,4
TcIVW	Rx timing window	-	0.3	-	0.3	-	0.3	-	0.3	UI*	1,2,3,4
VIHL_AC	CA AC input pulse amplitude pk-pk	210	-	210	-	190	-	180	-	mV	5,8
TcIPW	CA input pulse width	0.55		0.55		0.6		0.6		UI*	6

# DQ Termination Scheme



# Beyond LPDDR4

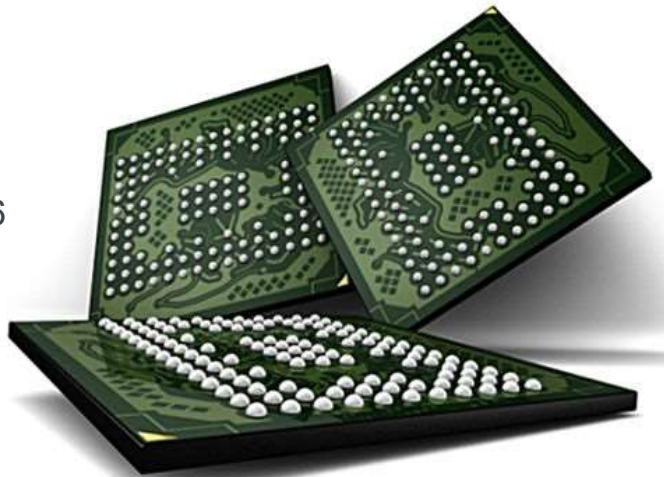
- Low Voltage LPDDR4:
  - Same VDD1, VDD2
  - Reduced VDDQ = 0.6 V (for high speed terminated signaling)  
VOH ~ 0.5 · VDDQ
  - Reduced VDDQ = 0.4 V (for unterminated full swing at lower frequencies)
  - VDDQ changing dynamically
  
- LPDDR5 ....





# Signal Access for LPDDR Memory Technologies

3/14/2016

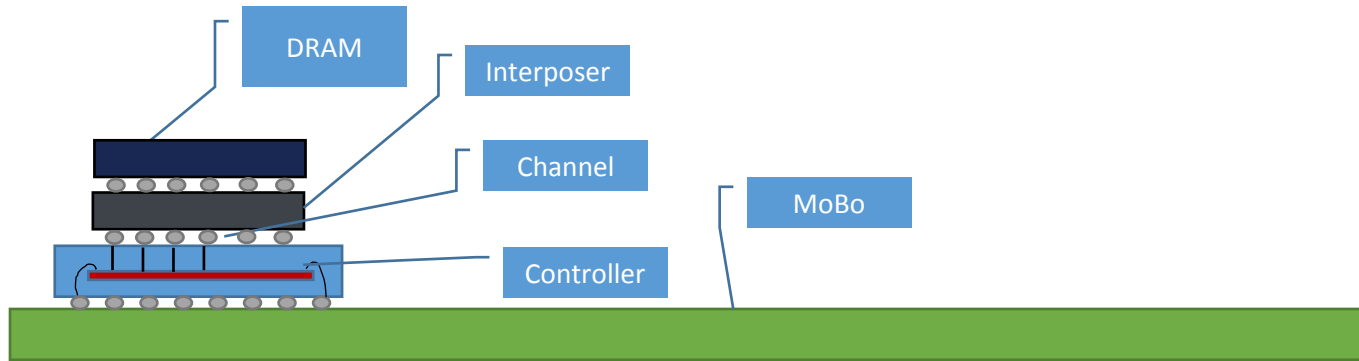
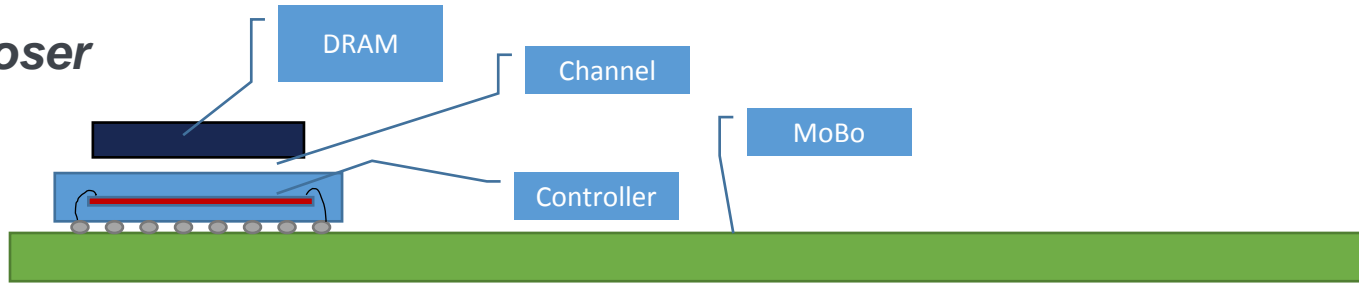


# Section Agenda

- Interposer
  - Need
  - Interposer Port Naming
  - Modelling
  - Interposer Type
  - Interposer Availability
  - De-Embedding
  - Tri-Modes Probes

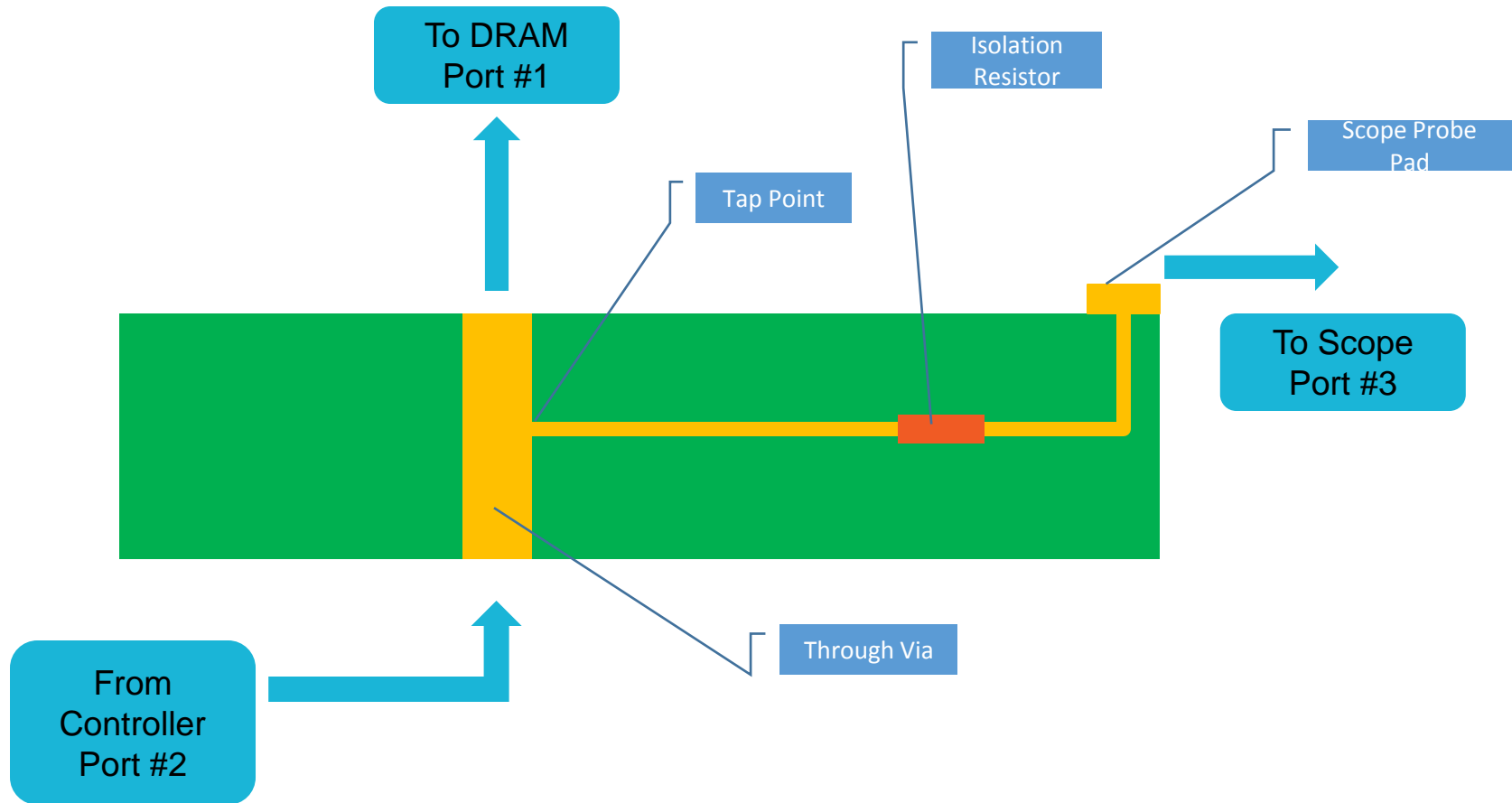
# Probing

## *Interposer*

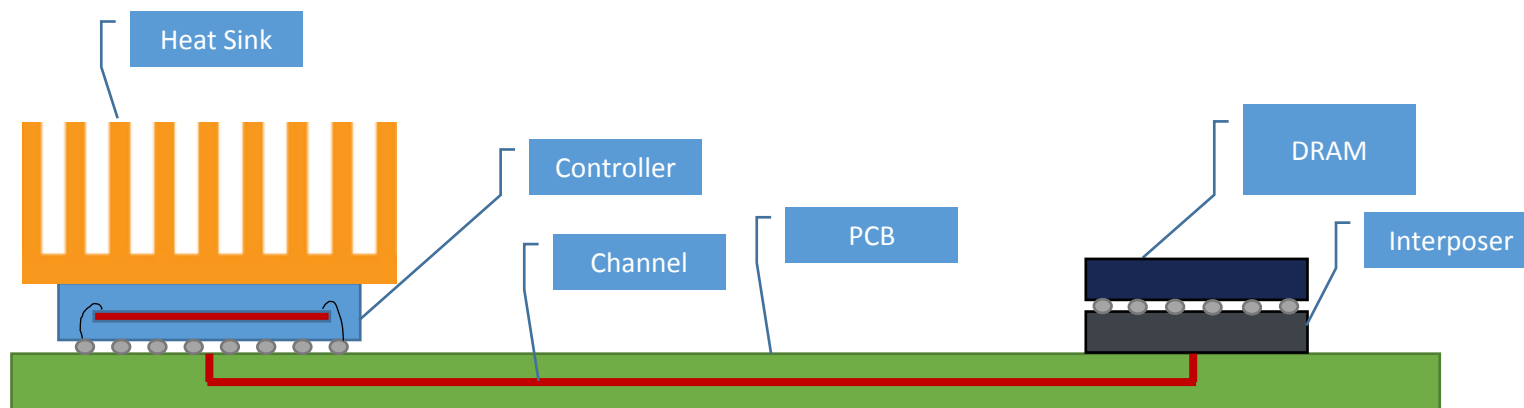


- An Interposer provides access to the signals for characterization and Debug
- Due to the density of the packages only a subset of all the signals are available for probing
- Custom probing solutions can be built if needed for specific applications

# Interposer Port Naming



# Modeling



- System level modeling is performed to study the signal behavior with probing solution in the channel path
- 2 port and 4 port S-parameter models that represent the probing system
- Two types of models represent the probing system
  - Loaded Models represent the case when the probe connected
  - Unloaded models represent the case when the probe is not connected

# Interposer Types for Scope Probing

## Socketed Interposers

- Large KoV (Keep out Volume)
- Easy to use with socket
- Access to more signals

## Solder Down Interposers

- Larger KoV
- Access to more signals
- Low reusability

## Edge Interposers

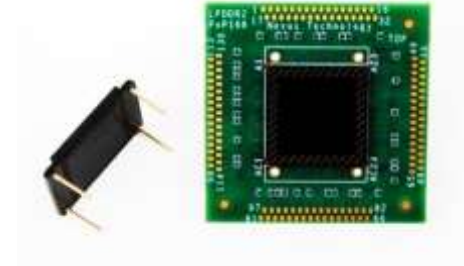
- Small KoV
- Access to less number of signals
- Low reusability

## Custom Interposers

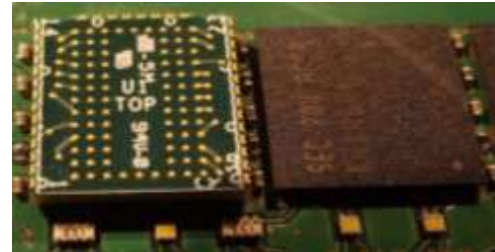
KoV as per design requirements  
Mechanicals to match custom socketing  
Signals as per specification



Solder Down interposer with Probe Pads



Socketed interposer for packages



Solder Down Interposer with Edge Style Probing



Socketed interposer with Probe Pads

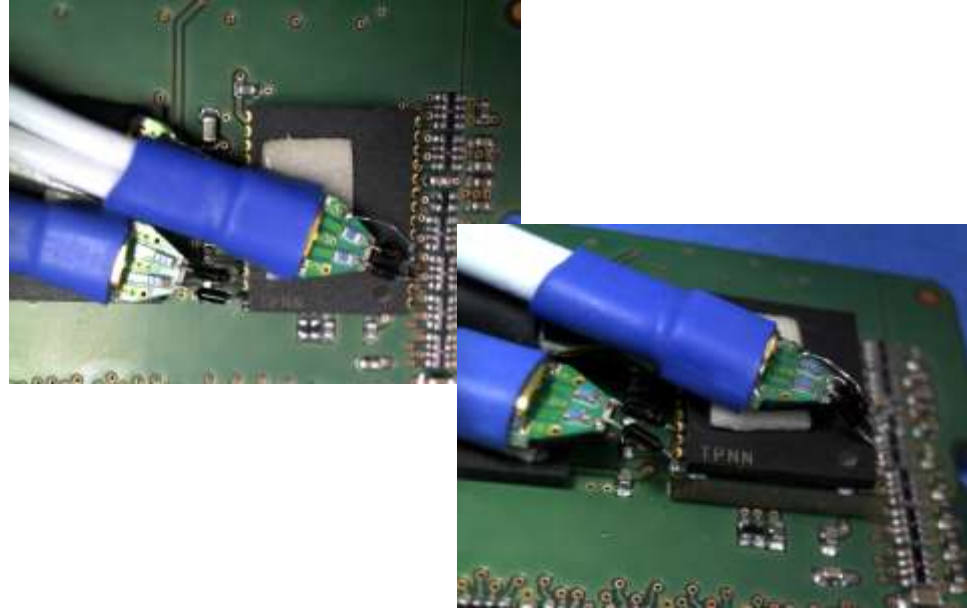
# Interposer Availability

Technology	Package / Form Factor
DDR2	Socketed – 60 Ball/ 84 Ball Solder-down – 60 Ball/ 84 Ball
DDR3	Socketed – 78 Ball/ 96 Ball Solder-down – 78 Ball/ 96 Ball Edge Probe – 78 Ball/ 96 Ball – Coming soon! DIMM Interposer for MSO SO-DIMM Interposer for MSO
DDR4	Socketed – 78 Ball/ 96 Ball Edge Probe – 78 Ball/ 96 Ball Edge Probe – 144 Ball – Coming soon! DIMM Interposer for MSO
LPDDR	Socketed – 60ball
LPDDR2	Socketed – 136 ball/168 ball/216 ball/240 ball
LPDDR3	Socketed – 216 ball Solder-down – 178 ball
LPDDR4	Socketed – 272 ball Edge Probe – 272 ball Solder-down – 200 Ball Solder-down – 366 Ball
GDDR5	Socketed – 170 ball Solder – down – 170 ball



# Probing LPDDR

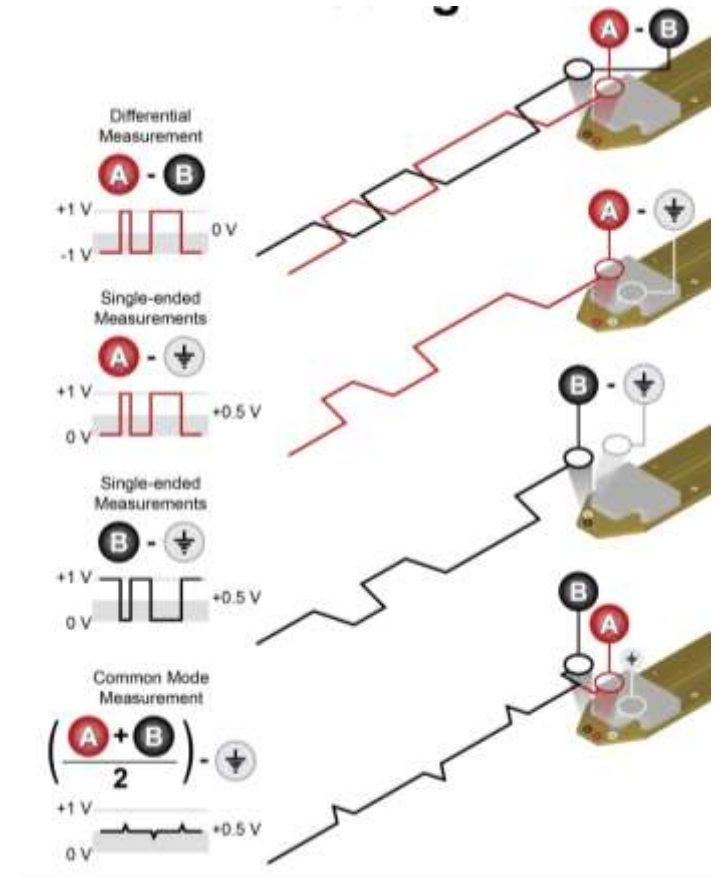
- Requirements
  - Multiple connections
  - Tight spaces
  - High performance
  - Solder-in connectivity
- Performance Probes
  - Consist of scope connection, >1m length cable, amplifier and attenuation stages
  - Accessory tips





# TriMode™ Probes

- TriMode, with a single probe-DUT connection, allows:
  - Traditional differential measurements
  - Independent single ended measurements on either input
    - V+ with respect to ground
    - V- with respect to ground
  - Direct common mode measurements
- Another use of TriMode
  - Connecting 2 single ended signals, such as DQ0 and DQ0
  - Switching between the data signals via the scope's UI for a measurement on each DQ



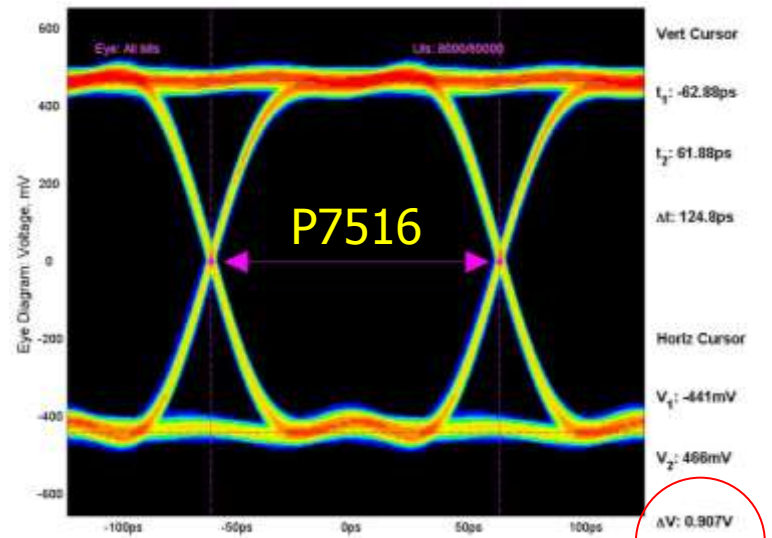
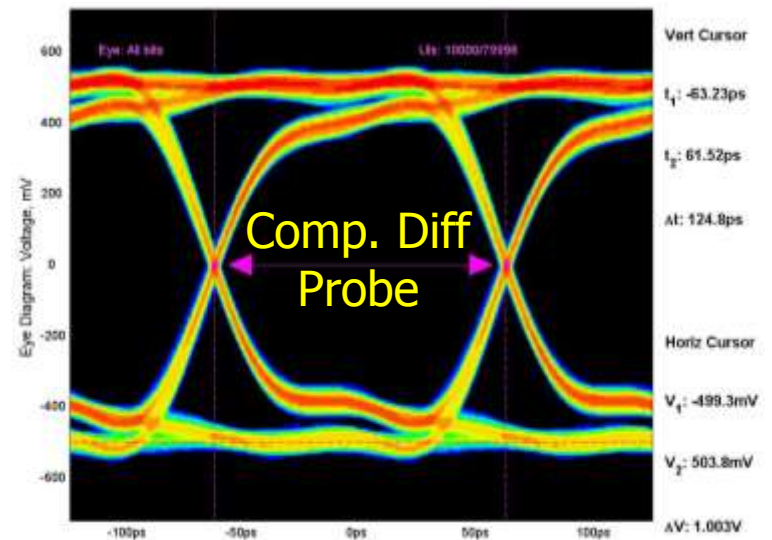
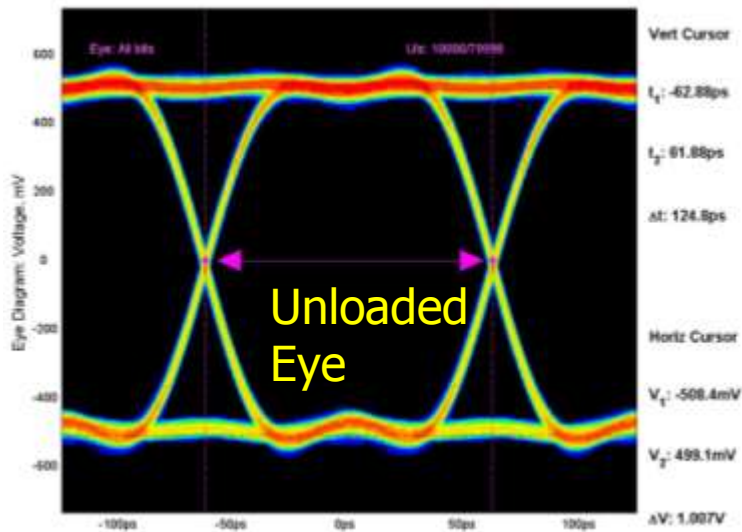
# Other Signal Access Challenges

- Connections between DIMM slots
- Connections inside of a closed chassis
- Crowded boards with large components blocking access to the test points

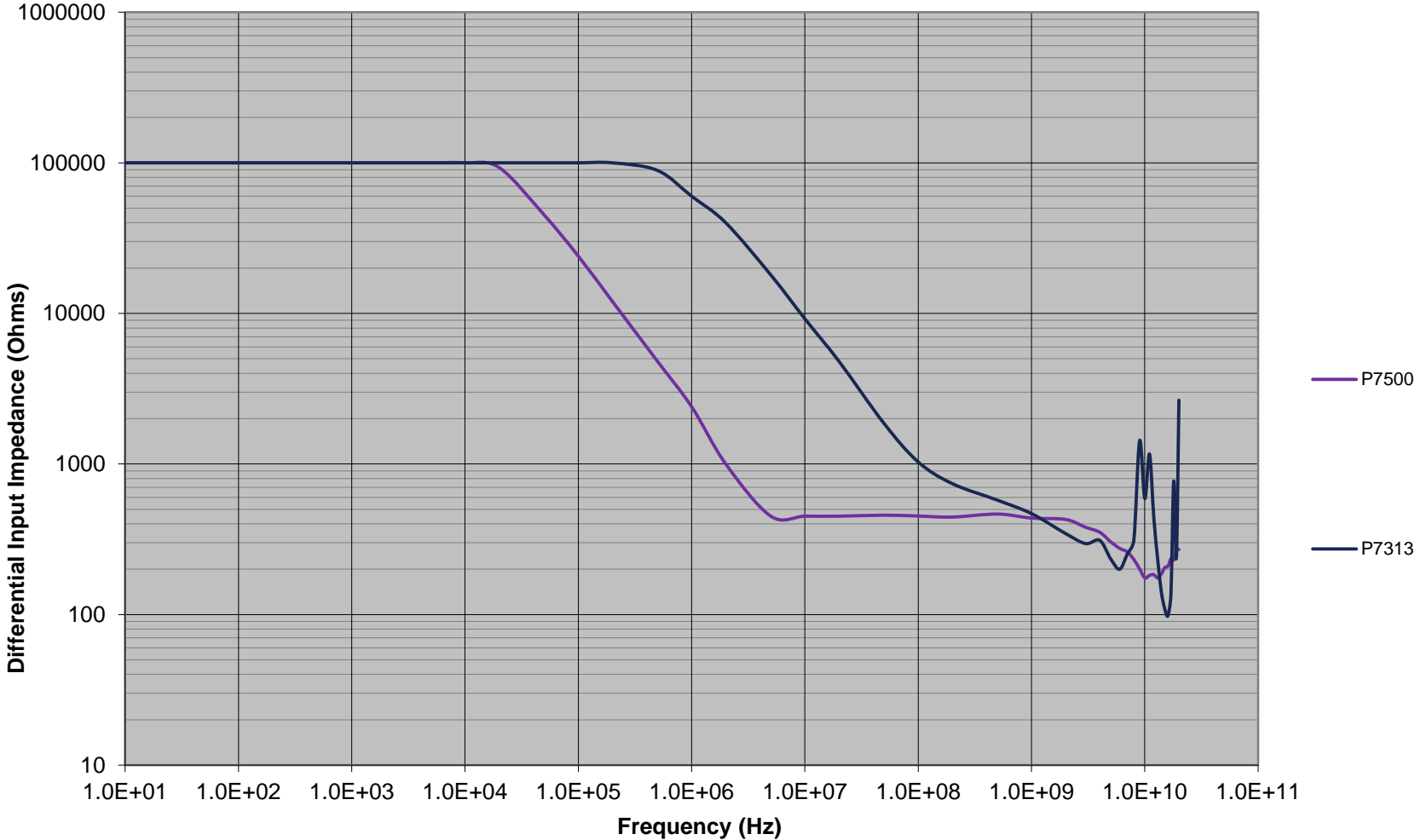


# Impact of attaching a probe

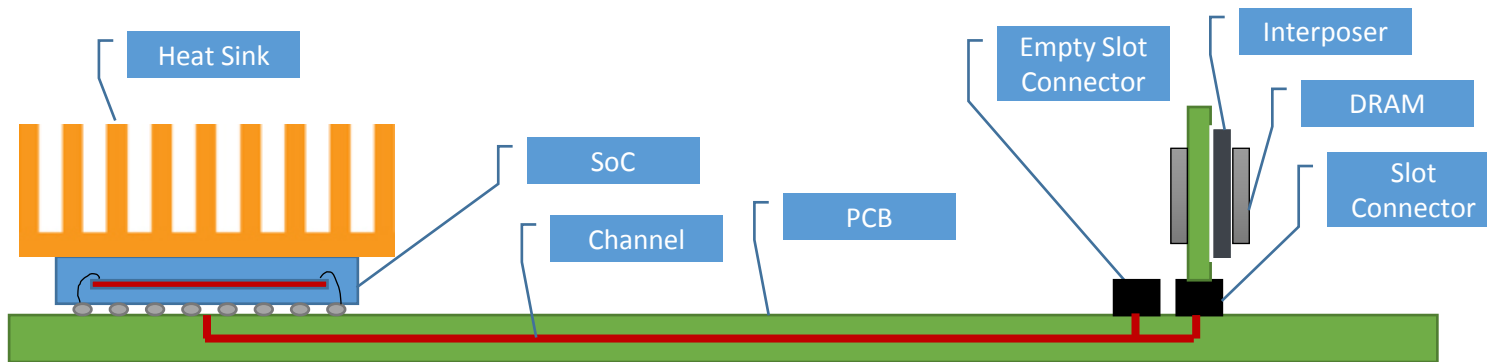
## 8Gb/s Eye



# Performance Probe Differential Input Impedance



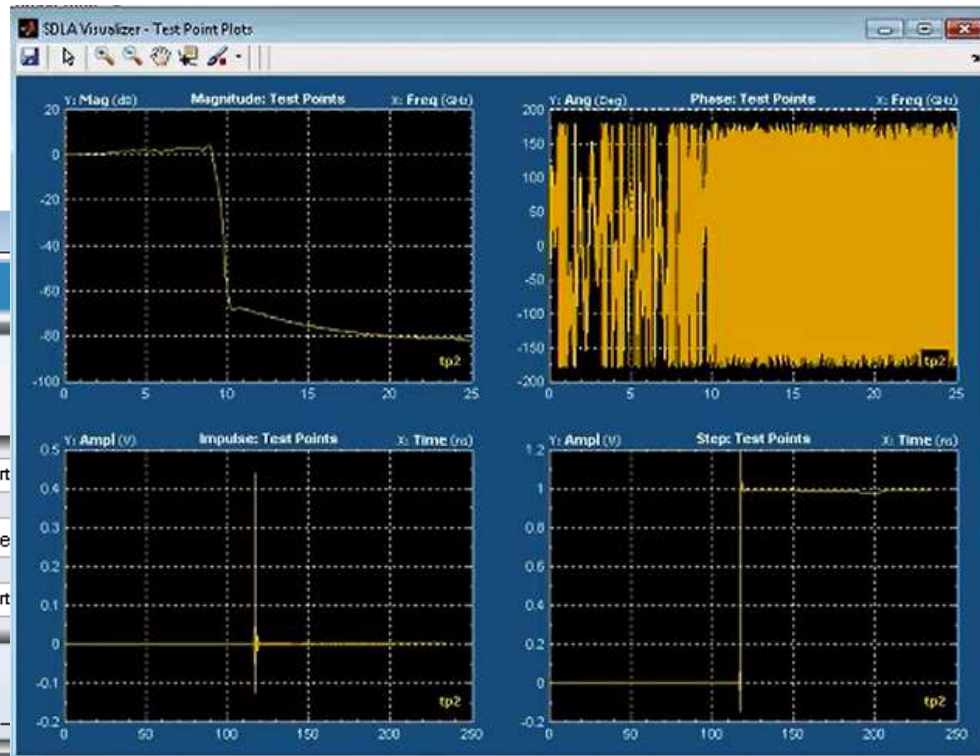
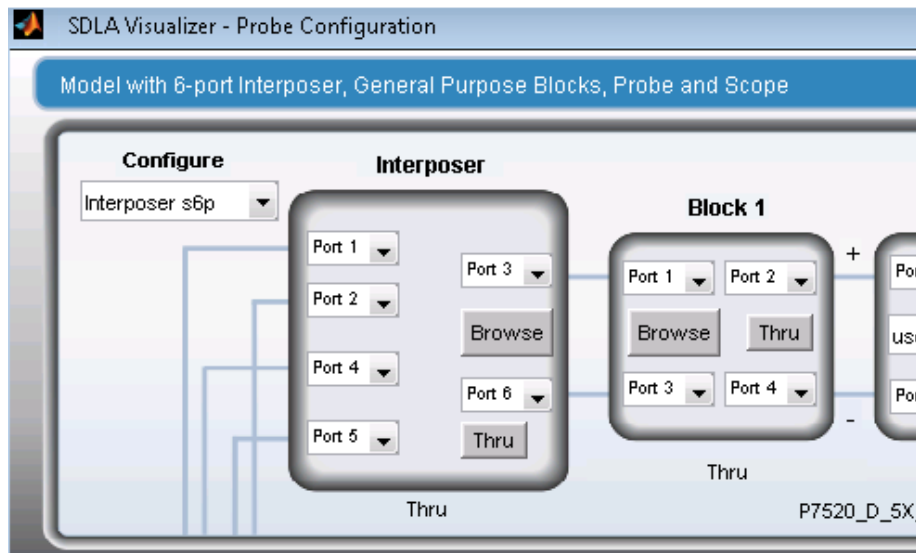
# De-embedding / Virtual Probing



- In order to remove the effects of the Interposer/Probe, De-embedding must be considered.
- S-Parameters of the objects that need to be de-embedded are required for de-embedding
- S-Parameters for the Interposer will be made available and can be used to create De-embed filters.
- S-parameters can be extracted
  - From the 3D models by simulation
  - Measuring on a real sample using a VNA or TDR method on sampling scope

# De-embed Filter

- Model the probing setup Use the S-Parameter Models to generate Filters
- Supports different blocks in the signal path including
  - Interposer
  - Probe / tip
  - RF Switch



# P7700 High Bandwidth TriMode™ Probe is coming.....

**NEW!** Active input directly at the probe tip

**NEW!** TekFlex™ accessories

- Improved access to tight test locations

**Best-in-Class** low loading for LPDDR and  
MIPI standard

**Industry's lowest** cost per connection





**Tektronix**

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Thank You!

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